# 10V Drive Nch MOSFET

## **R5013ANX**

#### ●Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (VGSS) guaranteed to be  $\pm 30$ V.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

### Applications

Switching

#### Packaging specifications

Code – Type Basic ordering unit (pieces) 500		Package	Bulk
Type Basic ordering unit (pieces) 500		Code	_
	Type	Basic ordering unit (pieces)	500
R5013ANX	R5013	0	

#### ● Absolute maximum ratings (Ta=25°C)

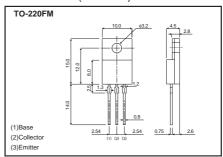
Parameter	Symbo	ol	Limits	Unit	
Drain-source voltage	VDSS		500	V	
Gate-source voltage	Vgss		±30	V	
Drain current	Continuous	ΙD	*3	±13	А
Diam current	Pulsed	IDP	*1	±52	А
Source current (Body Diode)	Continuous	Is	*3	13	А
	Pulsed	Isp	*1	52	А
Avalanche Current	las	*2	13	А	
Avalanche Energy	Eas	*2	46	mJ	
Total power dissipation	PD		50	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1% \*2 L $\div$  500µH, Voo=50V, Rc=25 $\Omega$ , Starting, Tch=25 $^{\circ}$ C \*3 Limited only by maximum tempterature allowed

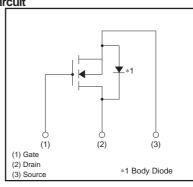
## Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.5	°C/W

#### ●Dimensions (Unit:mm)



●Inner circuit



## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	_	±100	nA	Vgs=±30V, Vds=0V	
Drain-source breakdown voltage	V(BR)DSS	500	_	_	V	In=1mA, Vgs=0V	
Zero gate voltage drain current	IDSS	_	_	100	μΑ	VDS=500V, VGS=0V	
Gate threshold voltage	VGS(th)	2.5	_	4.5	V	VDS=10V, ID=1mA	
Static drain-source on-state resistance	RDS(on)*	_	0.29	0.38	Ω	In=6.5A, Vgs=10V	
Forward transfer admittance	Yfs   *	4.0	_	-	S	In=6.5A, Vns=10V	
Input capacitance	Ciss	_	1300	_	pF	VDS=25V	
Output capacitance	Coss	_	500	_	pF	Vgs=0V	
Reverse transfer capacitance	Crss	_	40	-	pF	f=1MHz	
Turn-on delay time	td(on) *	_	30	_	ns	ID=6.5A, VDD ≒250V	
Rise time	tr *	_	32	-	ns	V <sub>GS</sub> =10V	
Turn-off delay time	td(off) *	_	90	_	ns	RL=38.5Ω	
Fall time	t <sub>f</sub> *	_	30	_	ns	R <sub>G</sub> =10Ω	
Total gate charge	Qg *	_	35	-	nC	V <sub>DD</sub> ≒250V	
Gate-source charge	Qgs *	_	8	_	nC	I <sub>D</sub> =13A   V <sub>G</sub> s=10V	
Gate-drain charge	Q <sub>gd</sub> *		15		nC	R <sub>L</sub> =19.2Ω / R <sub>G</sub> =10Ω	

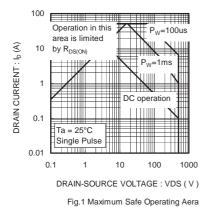
<sup>\*</sup> Pulsed

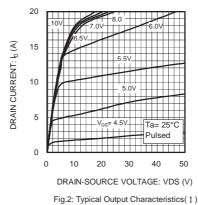
## ●Body diode characteristics (Source-drain) (Ta=25°C)

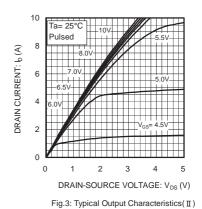
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	ı	1.5	V	I <sub>S</sub> = 13A, V <sub>GS</sub> =0V

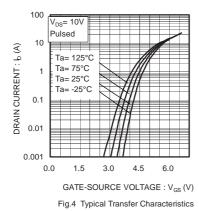
<sup>\*</sup> Pulsed

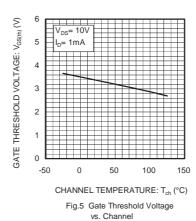
#### Electrical characteristic curves

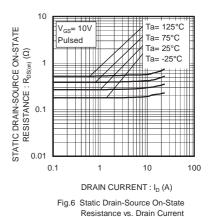


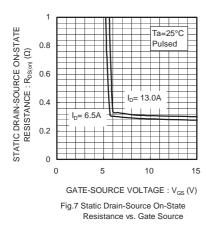


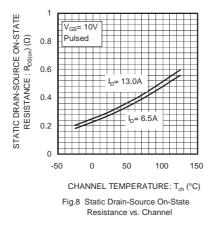


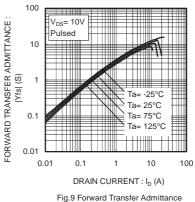


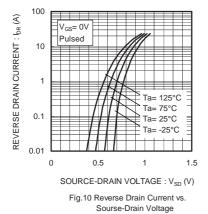


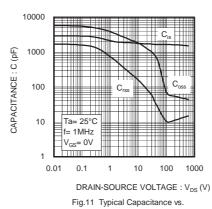




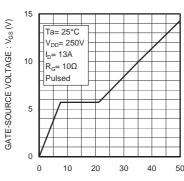




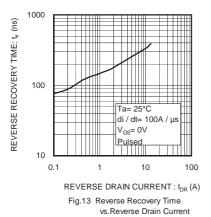


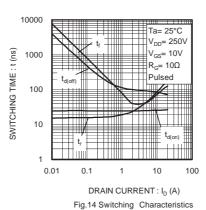


Drain-Source Voltage



TOTAL GATE CHARGE :  $\mathbf{Q}_{\mathrm{g}}$  (nC) Fig.12 Dynamic Input Characteristics





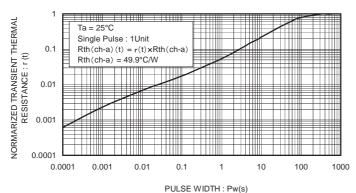


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

#### •Switching characteristics measurement circuit

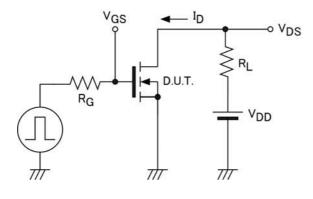


Fig.1 Switching time measurement circuit

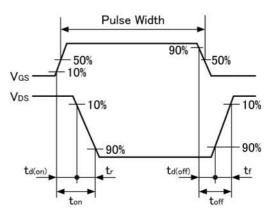


Fig.2 Switching waveforms

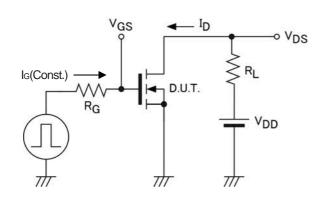


Fig.3 Gate charge measurement circuit

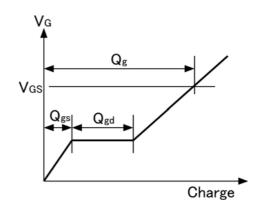


Fig.4 Gate charge waveform

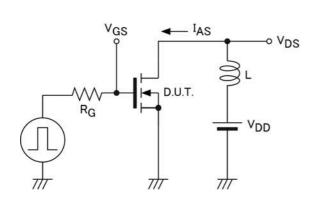


Fig.5 Avalanche measurement circuit

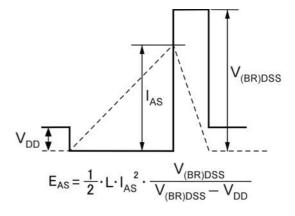


Fig.6 Avalanche waveform

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